NSN 5961-01-338-2168

Photo Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-338-2168 Inclosure Material:

Inclosure Material:
Metal
Internal Configuration:
Junction contact
Mounting Method:
Terminal
Semiconductor Material:
Gallium arsenide phosphide
Voltage Rating In Volts Per Characteristic:
6.3 forward voltage, dc
Current Rating Per Characteristic:
150.00 milliamperes forward current, average absolute
Special Features:
Junction pattern arrangement: pn
Shelf Life:
N/a
Unit Of Measure:
Demilitarization:
Yes - demil/mli
Fiig:
A110a0